

TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM6GZ47, SM6JZ47, SM6GZ47A, SM6JZ47A

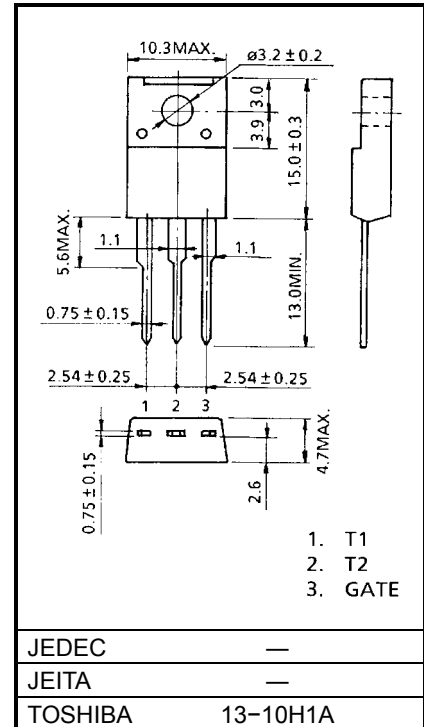
AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage : $V_{DRM} = 400, 600V$
- R.M.S ON-State Current : $I_T (RMS) = 6A$
- High Commutating (dv / dt)
- Isolation Voltage : $V_{ISOL} = 1500V AC$

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	SM6GZ47 SM6GZ47A	V_{DRM} 400	V
	SM6JZ47 SM6JZ47A	600	
R.M.S On-State Current (Full Sine Waveform $T_c = 90^\circ C$)	$I_T (RMS)$	6	A
Peak One Cycle Surge On-State Current (Non-Repetitive)	I_{TSM}	60 (50Hz)	A
		66 (60Hz)	
$I^2 t$ Limit Value	$I^2 t$	18	$A^2 s$
Critical Rate of Rise of On-State Current (Note 1)	di / dt	50	$A / \mu s$
Peak Gate Power Dissipation	P_{GM}	5	W
Average Gate Power Dissipation	$P_G (AV)$	0.5	W
Peak Gate Voltage	V_{FGM}	10	V
Peak Gate Current	I_{GM}	2	A
Junction Temperature	T_j	-40~125	$^\circ C$
Storage Temperature Range	T_{stg}	-40~125	$^\circ C$
Isolation Voltage (AC, $t = 1min.$)	V_{ISOL}	1500	V

Unit: mm



Weight: 1.7g

Note 1: di / dt test condition

$V_{DRM} = 0.5 \times \text{Rated}$

$I_{TM} \leq 9A$

$t_{gw} \geq 10\mu s$

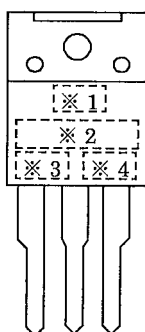
$t_{gr} \leq 250ns$

$i_{gp} = I_{GT} \times 2.0$

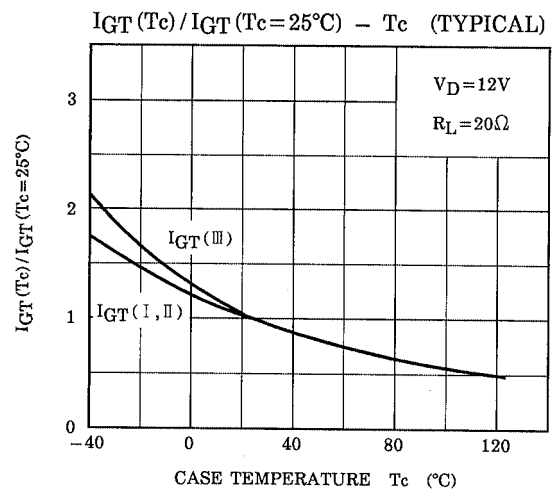
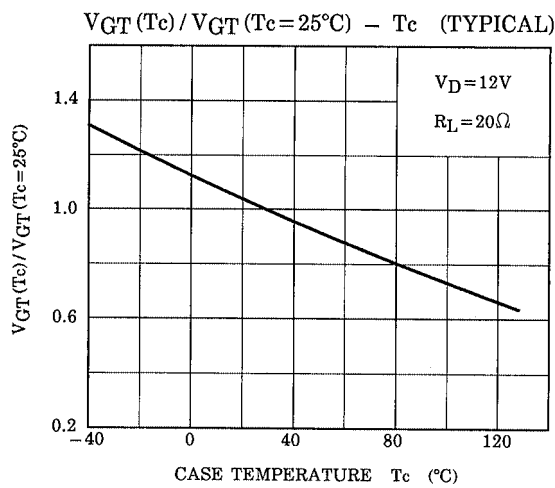
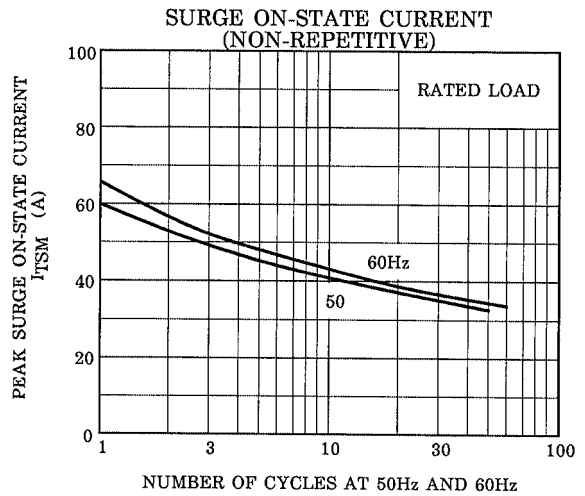
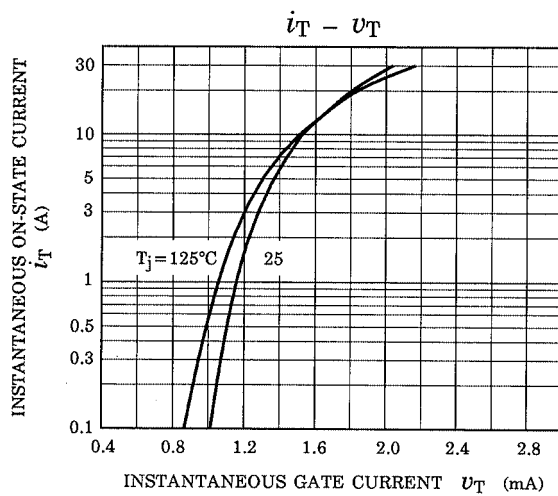
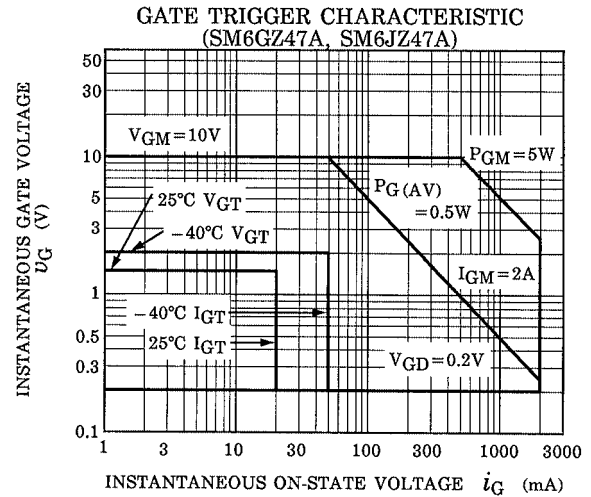
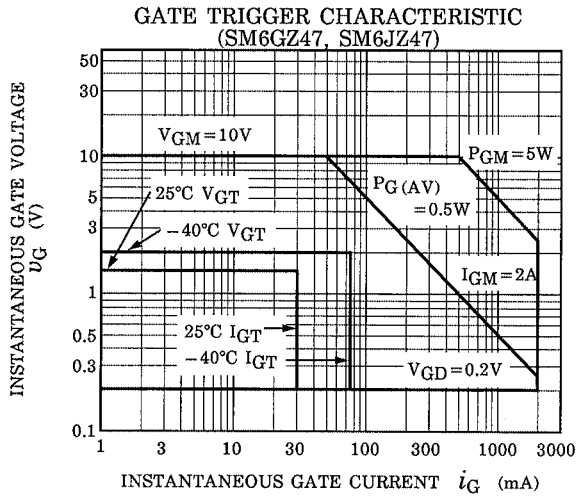
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

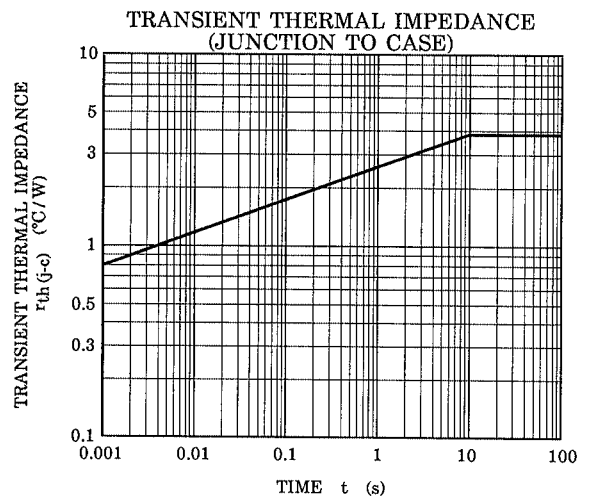
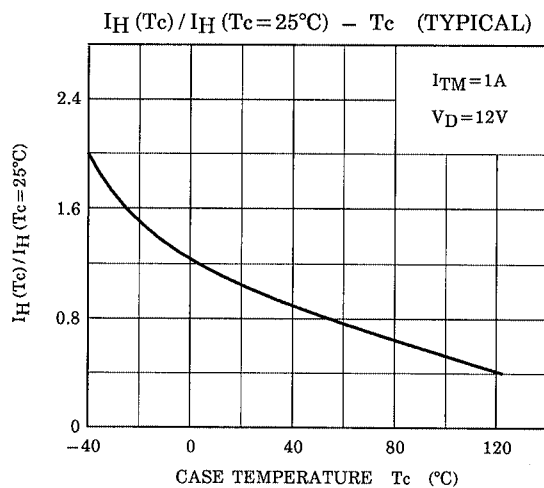
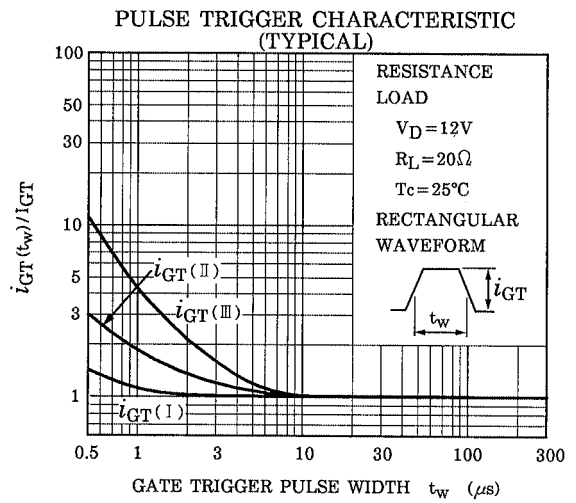
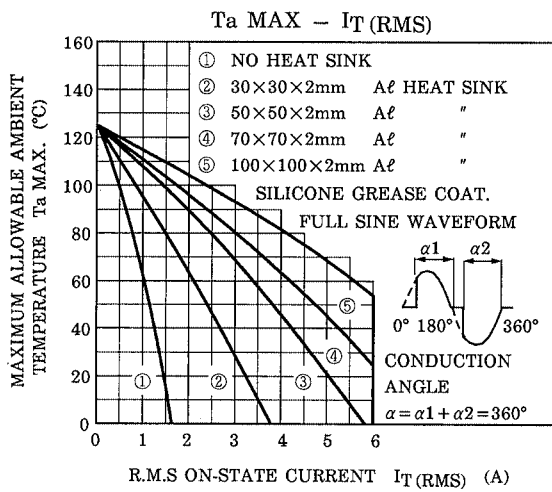
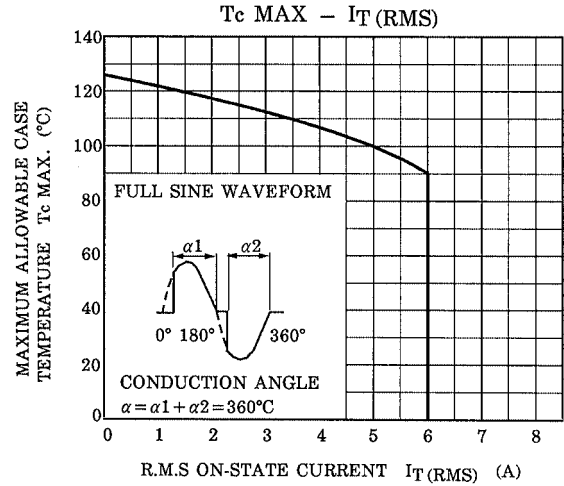
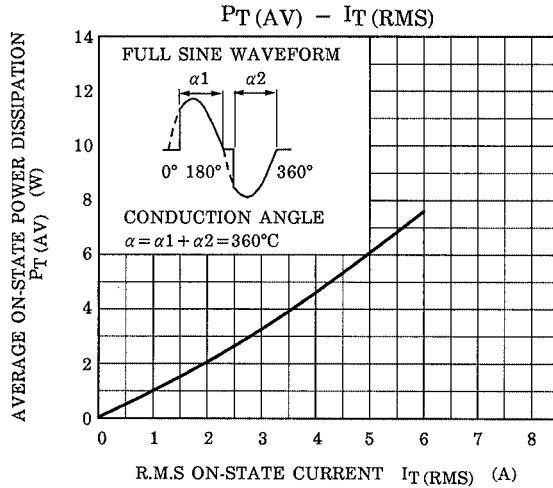
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT	
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} = Rated		—	—	20	μA	
Gate Trigger Voltage		I	V _{GT}	V _D = 12V R _L = 20Ω	T2 (+), Gate (+)	—	—	1.5	V
		II			T2 (+), Gate (–)	—	—	1.5	
		III			T2 (–), Gate (–)	—	—	1.5	
		IV			T2 (–), Gate (+)	—	—	—	
Gate Trigger Current	SM6GZ47 SM6JZ47	I	I _{GT}	V _D = 12V R _L = 20Ω	T2 (+), Gate (+)	—	—	30	mA
		II			T2 (+), Gate (–)	—	—	30	
		III			T2 (–), Gate (–)	—	—	30	
		IV			T2 (–), Gate (+)	—	—	—	
	SM6GZ47A SM6JZ47A	I			T2 (+), Gate (+)	—	—	20	
		II			T2 (+), Gate (–)	—	—	20	
		III			T2 (–), Gate (–)	—	—	20	
		IV			T2 (–), Gate (+)	—	—	—	
Peak On-State Voltage		V _{TM}	I _{TM} = 9A		—	—	1.5	V	
Gate Non-Trigger Voltage		V _{GD}	V _D = Rated, T _c = 125°C		0.2	—	—	V	
Holding Current		I _H	V _D = 12V, I _{TM} = 1A		—	—	50	mA	
Thermal Resistance		R _{th} (j-c)	Junction to Case		—	—	3.8	°C / W	
Critical Rate of Rise of Off-State Voltage	SM6GZ47 SM6JZ47	dv / dt	V _{DRM} = Rated, T _j = 125°C Exponential Rise		—	300	—	V / μs	
	SM6GZ47A SM6JZ47A				—	200	—		
Critical Rate of Rise of Off-State Voltage at Commutation	SM6GZ47 SM6JZ47	(dv / dt) c	V _{DRM} = 400V, T _j = 125°C (di /dt) c = -3.3A / ms		10	—	—	V / μs	
	SM6GZ47A SM6JZ47A				4	—	—		

MARKING



* NUMBER	SYMBOL		MARK
* 1	TOSHIBA PRODUCT MARK		
* 2	TYPE	SM6GZ47, SM6GZ47A	M6GZ47
		SM6JZ47, SM6JZ47A	M6JZ47
* 3	SM6GZ47A, SM6JZ47A		A
* 4	Lot Number Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year)		Example 8A : January 1998 8B : February 1998 8L : December 1998





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